

DO-35 Glass Switching Diode

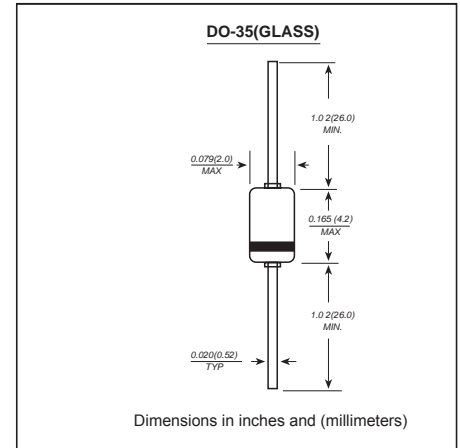
VOLTAGE RANGE: 75V
PEAK PULSE POWER: 500mW

Features

- Fast Switching Device (TRR <4.0 nS)
- Power Dissipation of 500mW
- High Stability and High Reliability
- Low reverse leakage

Mechanical Data

- Case: DO-35 Glass Case
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25 C ambient temperature unless otherwise specified

Parameters	Symbol	Value	Unit
Reverse Voltage	V _R	75	V
Peak Reverse Voltage	V _{RM}	100	V
Power Dissipation	P _d	500	mW
Operating junction temperature	T _j	175	°C
Storage temperature range	T _s	-65+200	°C
Working Inverse Voltage	W _{IV}	75	V
Average Rectified Current	I _o	150	mA
Non-repetitive Peak Forward Current @ t<1s and T _j =25°C	I _{FM}	450	mA

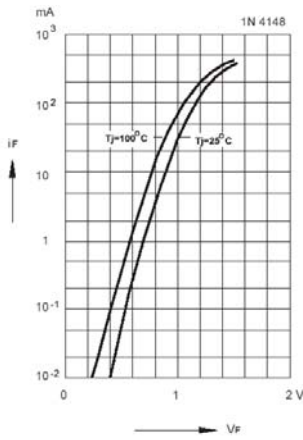
Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

Electrical Specification (T_A=25°C unless otherwise specified)

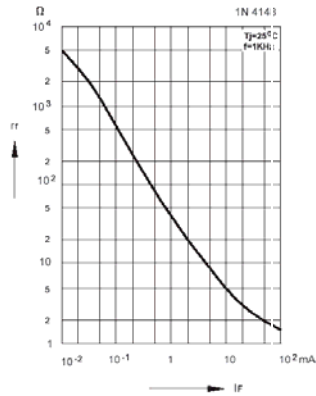
Symbols	Parameter	Test Condition	Limits		Unit
			Min	Max	
BV	Breakdown Voltage	IR=100uA	100		V
		IR=5uA	75		
IR	Reverse Leakage Current	VR=20V	---	25	nA
		VR=75	---	5	uA
VF	Forward Voltage	1N4448/1N914B IF=5mA	0.62	0.72	V
		1N4148 IF=10mA	---	1	
		1N4448/1N914B IF=100mA	---	1	
TRR	Reverse Recovery Time	IF= 10mA, IR=1.0mA RL=100Ω IRR=1mA	---	4	nS
C	Capacitance	VR=0V, f=1MHZ	---	4	pF

Typical Characteristics

Forward characteristics

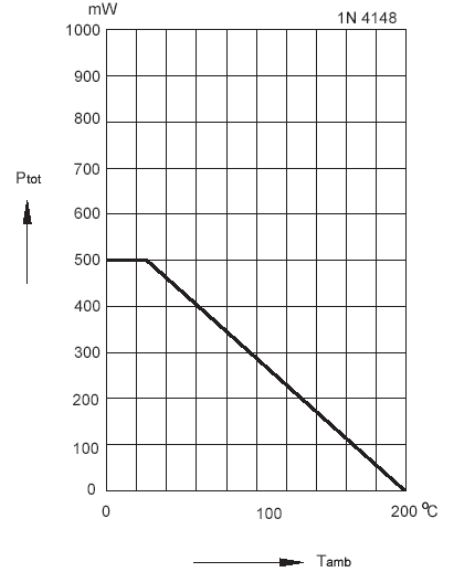


Dynamic forward resistance versus forward current

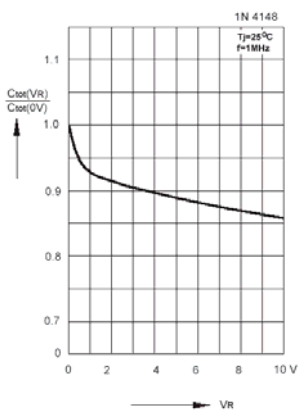


Admissible power dissipation versus ambient temperature

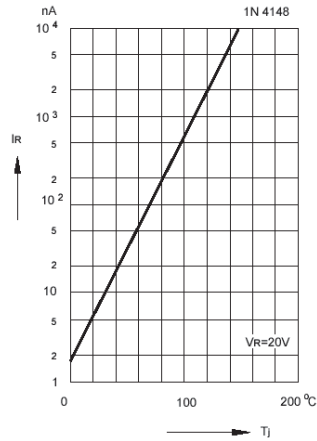
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Relative capacitance versus reverse voltage



Leakage current versus junction temperature



Admissible repetitive peak forward current versus pulse duration Valid provided that

leads at a distance of 8 mm from case are kept at ambient temperature

